

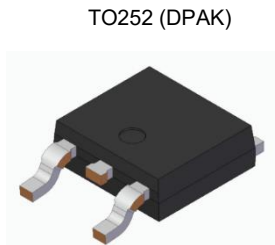
Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
55V	12mΩ @ V _{GS} = 10V	80A
	18mΩ @ V _{GS} = 4.5V	65A

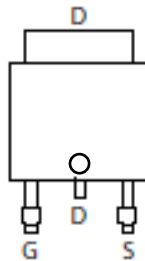
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

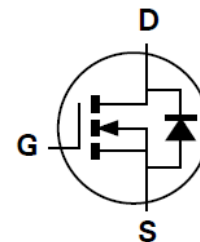
- Engine management systems
- Body control electronics
- DC/DC converters



Top View



Pinout Top View



Equivalent Circuit

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures more Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMNH6011LK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

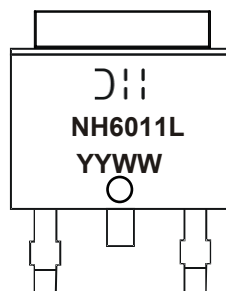
- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.33 grams (Approximate)

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMNH6011LK3Q-13	TO252 (DPAK)	2,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



 = Manufacturer's Marking
 NH6011L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 25 = 2025)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	55	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 7), V _{GS} = 10V	I _D	80 50	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	180	A
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	80	A
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	54	A
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	147	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	80	°C/W
Total Power Dissipation (Note 6)	P _D	3.0	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	42	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	1.1	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	55	—	—	V	V _{GS} = 0, I _D = 250μA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 55V, V _{GS} = 0
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	2	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8.3	12	mΩ	V _{GS} = 10V, I _D = 25A
		—	9.0	18		V _{GS} = 4.5V, I _D = 25A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0, I _S = 1.7A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	3,077	—	pF	V _{DS} = 30V, V _{GS} = 0, f = 1MHz
Output Capacitance	C _{oss}	—	331	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	127	—	pF	
Gate Resistance	R _g	—	1.7	—	Ω	V _{DS} = 0, V _{GS} = 0, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	23.4	—	nC	V _{DS} = 30V, I _D = 25A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	49.1	—	nC	
Gate-Source Charge	Q _{gs}	—	5.3	—	nC	
Gate-Drain Charge	Q _{gd}	—	9.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.9	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _G = 3Ω, I _D = 25A
Turn-On Rise Time	t _R	—	8.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	28.2	—	ns	
Turn-Off Fall Time	t _F	—	10.2	—	ns	
Body Diode Reverse-Recovery Time	t _{RR}	—	30.1	—	ns	I _F = 25A, di/dt = 100A/μs
Body Diode Reverse-Recovery Charge	Q _{RR}	—	25.7	—	nC	I _F = 25A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

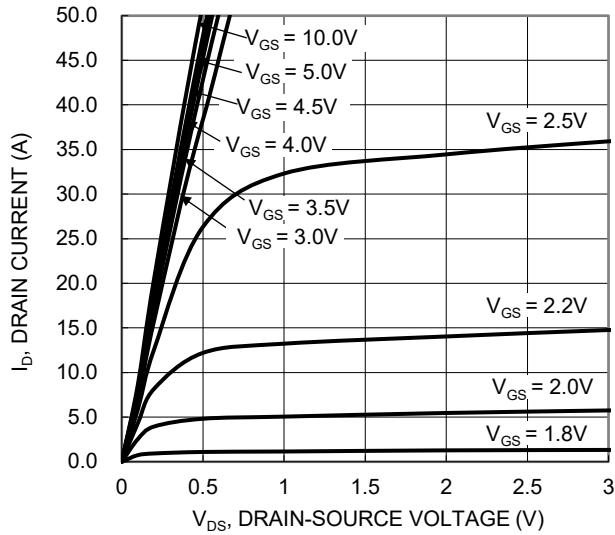


Figure 1. Typical Output Characteristic

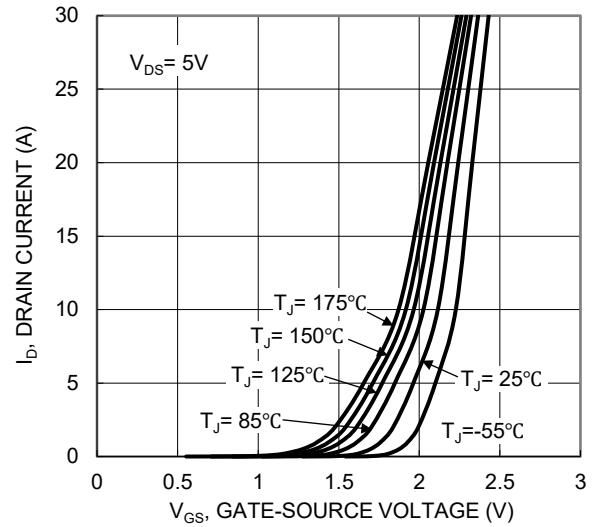


Figure 2. Typical Transfer Characteristic

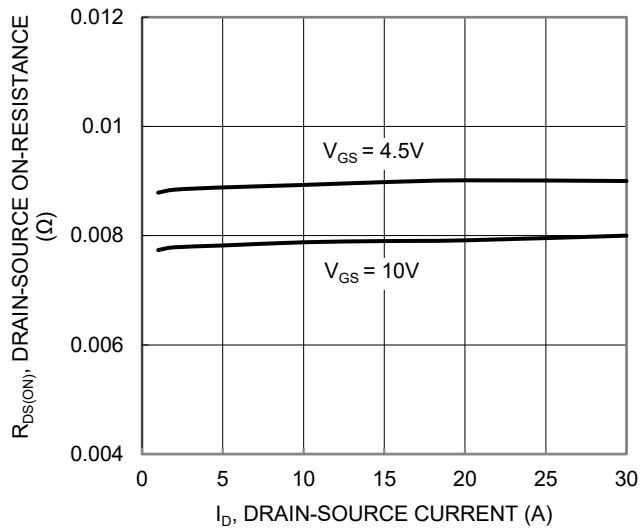


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

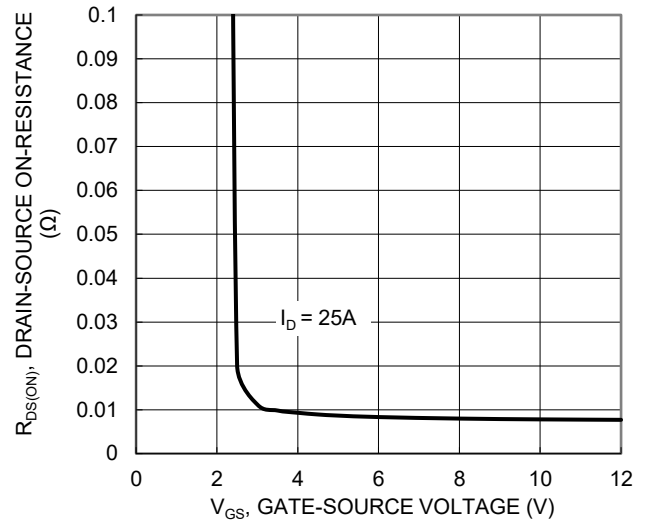


Figure 4. Typical Transfer Characteristic

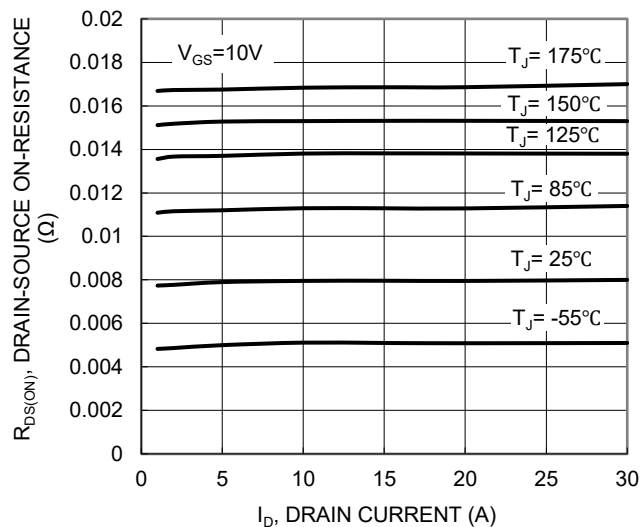


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

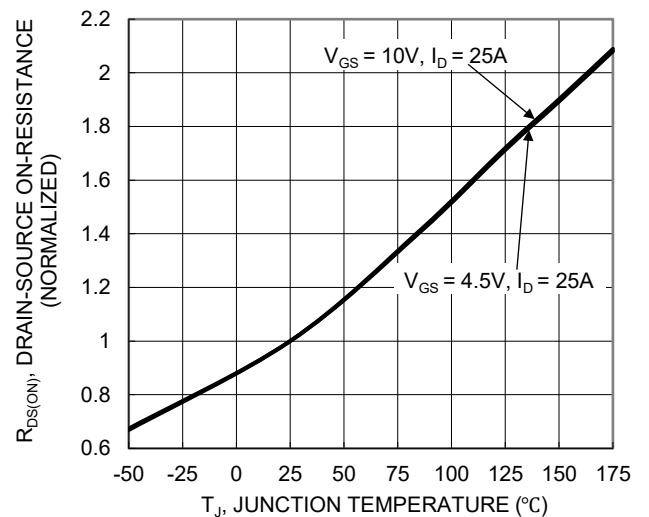


Figure 6. On-Resistance Variation with Temperature

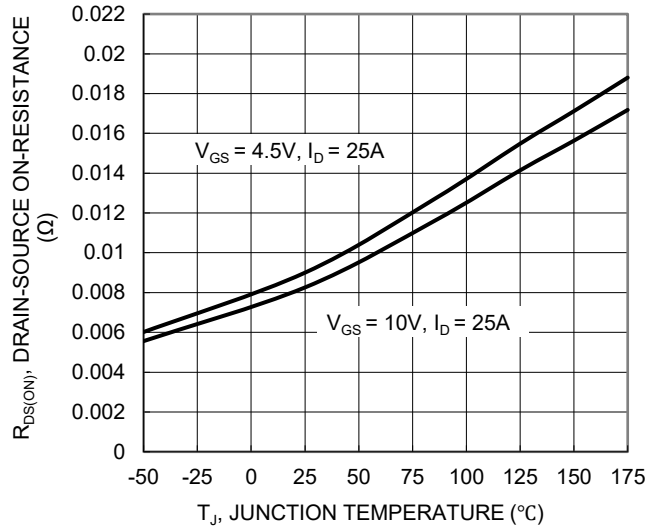


Figure 7. On-Resistance Variation with Temperature

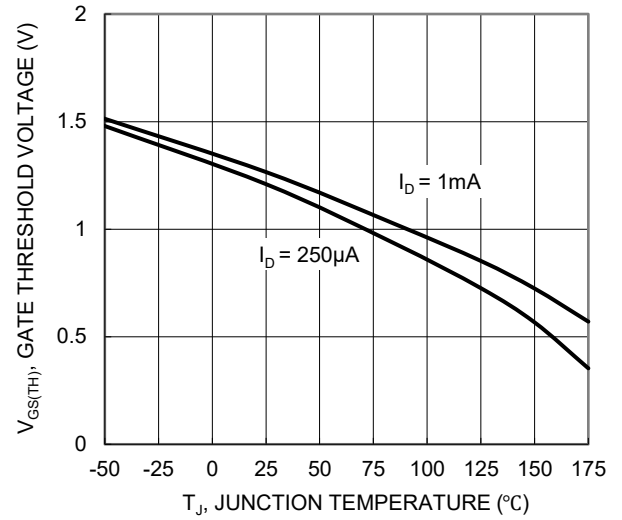


Figure 8. Gate Threshold Variation vs. Junction Temperature

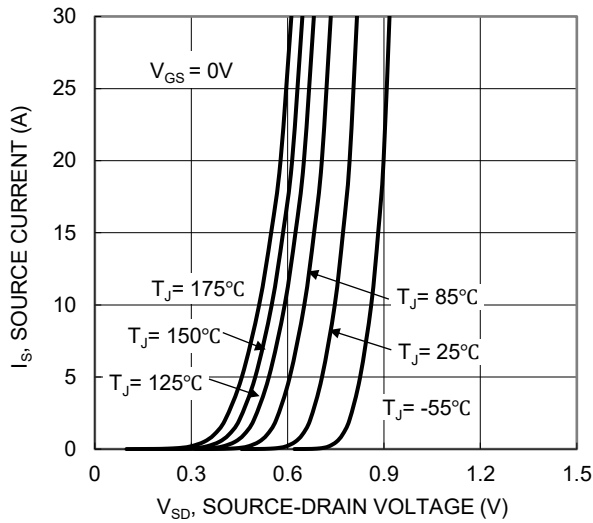


Figure 9. Diode Forward Voltage vs. Current

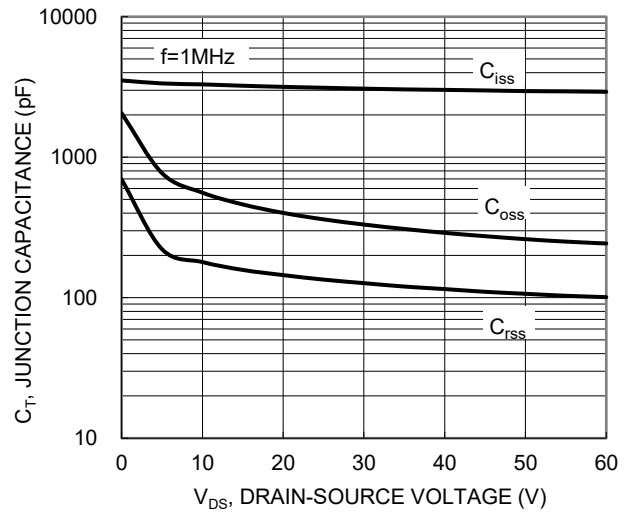


Figure 10. Typical Junction Capacitance

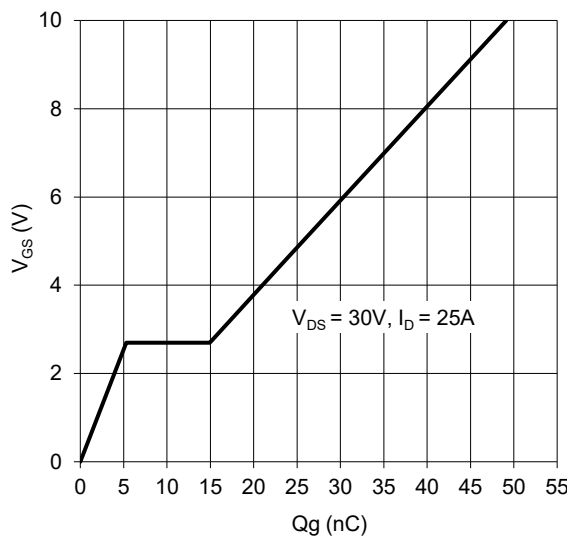


Figure 11. Gate Charge

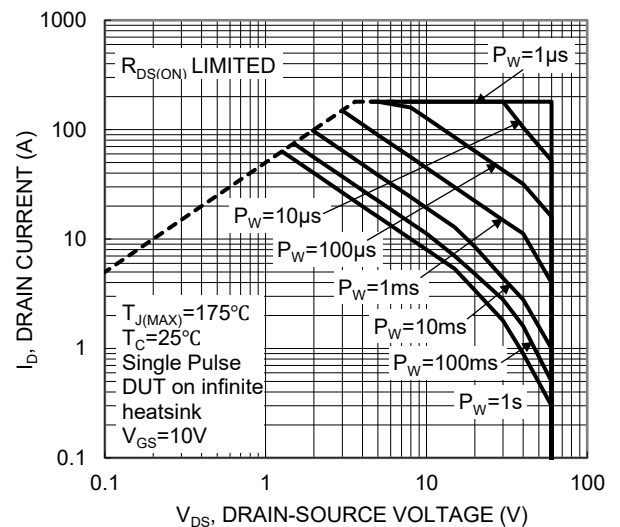


Figure 12. SOA, Safe Operation Area

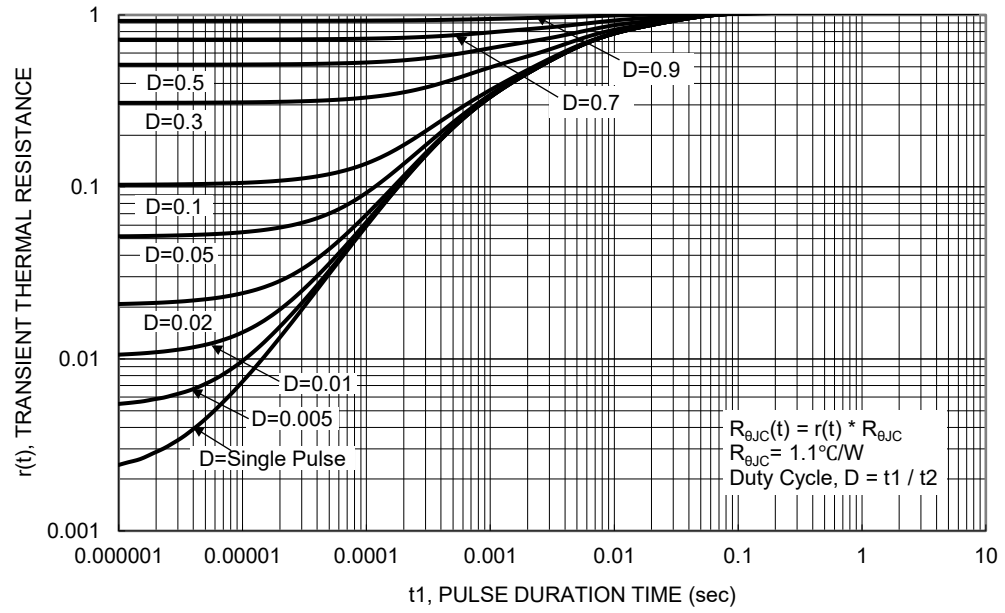
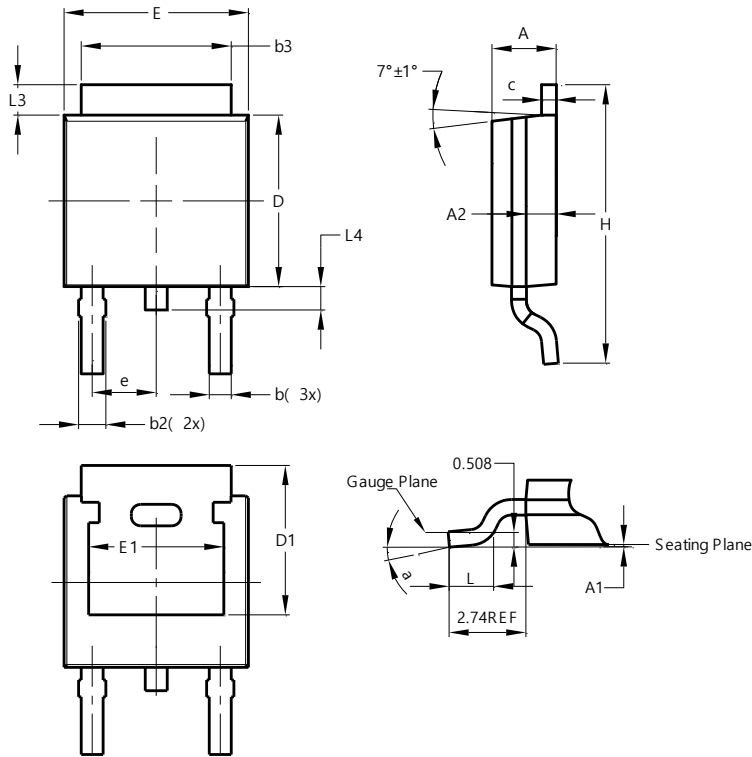


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

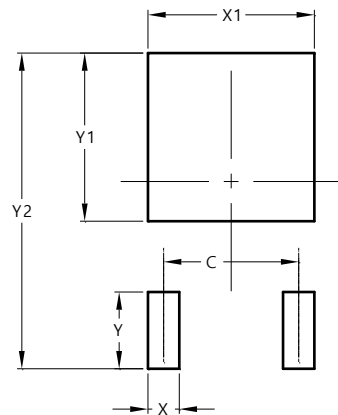


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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